

**MMBA812M4****PNP EPITAXIAL SILICON TRANSISTOR**

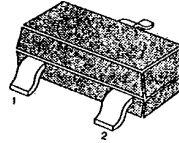
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**GENERAL PURPOSE TRANSISTOR****ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CB0}$	50	V
Collector-Emitter Voltage	$V_{CE0}$	40	V
Emitter-Base Voltage	$V_{EB0}$	5	V
Collector Current	$I_C$	100	mA
Collector Dissipation	$P_C$	350	mW
Storage Temperature	$T_{stg}$	150	$^\circ\text{C}$

• Refer to MMBT5086 for graphs

SOT-23



1. Base 2. Emitter 3. Collector

**ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ\text{C}$ )**

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=40\text{V}, I_E=0$		100	nA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5\text{V}, I_C=0$		100	nA
DC Current Gain	$h_{FE}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	90	180	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=30\text{mA}, I_B=3\text{mA}$		0.5	V
Base-Emitter On Voltage	$V_{BE(on)}$	$I_C=1\text{mA}, V_{CE}=6\text{V}$		0.8	V

Marking

